

IN THE CLAIMS:

Please retain claims 1, 4, 5 and 6 as set forth below.

1. (Previously Amended) A dry etching method comprising the step of:

dry-etching a formed film of tungsten through its entire thickness as originally formed using only a single mixed gas including a fluorine-containing gas that includes a compound having fluorine and carbon in a molecule, chlorine or hydrogen bromide, oxygen, and nitrogen,

wherein said fluorine-containing gas has a structure that a ratio of fluorine atoms with respect to elements of the gas molecule except for fluorine is four or less when the composition of the fluorine molecule is M_xF_y , $Y/X \leq 4$ where M is an element except for fluorine atom and F is fluorine, and the total number of fluorine atoms in elements constituting said gas molecule is four or less.

2. (Previously Cancelled)

3. (Previously Cancelled)

4. (Previously Amended) A method of manufacturing a semiconductor apparatus comprising the steps of:

laminating upwards a polycrystal silicon film or an amorphous silicon film, a tungsten nitride film or a titanium nitride film, and a tungsten film on a silicon substrate; and

performing a dry-etching of said tungsten nitride film through its entire thickness as originally formed, or said titanium nitride film and said tungsten film through its entire thickness as originally formed, with only a single mixed gas containing fluorine-containing gas that includes a compound

having fluorine and carbon in a molecule, chlorine or hydrogen bromide, oxygen and nitrogen so that a gate electrode is formed, wherein said fluorine-containing gas has a structure that a ratio of fluorine atoms with respect to elements of the gas molecule except for fluorine is four or less when the composition of the fluorine molecule is M_xF_y , $Y/X \leq 4$ where M is an element except for fluorine atom and F is fluorine, and the total number of fluorine atoms in elements constituting said gas molecule is four or less.

5. (Original) A method of manufacturing a semiconductor apparatus according to claim 4, wherein said gate electrode is formed by dry-etching said polycrystal silicon film or said amorphous silicon film with gas which does not contain fluorine.

6. (Previously Amended) A method of manufacturing a semiconductor apparatus according to claim 4, wherein a mask is formed by silicon oxide or silicon nitride, and said gate electrode is formed by dry etching using said mask.

7. (Previously Cancelled)

8. (Previously Cancelled)